



**THE DATASHEET OF  
NSS20201LT1G**



# NSS20201LT1G, NSV20201LT1G

## 20 V, 4.0 A, Low $V_{CE(sat)}$ NPN Transistor

ON Semiconductor's e<sup>2</sup>PowerEdge family of low  $V_{CE(sat)}$  transistors are miniature surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

### Features

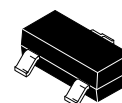
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



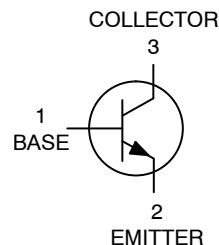
ON Semiconductor®

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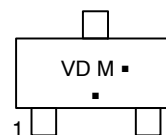
**20 VOLTS 4.0 AMPS  
NPN LOW  $V_{CE(sat)}$  TRANSISTOR  
EQUIVALENT  $R_{DS(on)}$  37 mΩ**



**SOT-23 (TO-236)  
CASE 318  
STYLE 6**



### MARKING DIAGRAM



VD = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping†
NSS20201LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSV20201LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NSS20201LT1G, NSV20201LT1G

## MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	20	Vdc
Collector-Base Voltage	$V_{CBO}$	20	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current – Continuous	$I_C$	2.0	A
Collector Current – Peak	$I_{CM}$	4.0	A
Electrostatic Discharge	ESD	HBM Class 3B MM Class C	

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$ (Note 1)	460 3.7	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 1)	270	$^\circ\text{C}/\text{W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$ (Note 2)	540 4.3	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 2)	230	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces.
2. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces.

# NSS20201LT1G, NSV20201LT1G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	20	–	–	V <sub>dc</sub>
Collector – Base Breakdown Voltage (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	20	–	–	V <sub>dc</sub>
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 0.1 mA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	–	–	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = 20 V <sub>dc</sub> , I <sub>E</sub> = 0)	I <sub>CBO</sub>	–	–	0.1	μA <sub>dc</sub>
Emitter Cutoff Current (V <sub>EB</sub> = 6.0 V <sub>dc</sub> )	I <sub>EBO</sub>	–	–	0.1	μA <sub>dc</sub>

### ON CHARACTERISTICS

DC Current Gain (Note 3) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 2.0 V) (I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 2.0 V) (I <sub>C</sub> = 1.0 A, V <sub>CE</sub> = 2.0 V) (I <sub>C</sub> = 2.0 A, V <sub>CE</sub> = 2.0 V)	h <sub>FE</sub>	200 200 200 200	– 360 – –	– – – –	
Collector – Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = 0.1 A, I <sub>B</sub> = 0.010 A) (I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 0.100 A) (I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 0.010 A) (I <sub>C</sub> = 2.0 A, I <sub>B</sub> = 0.200 A)	V <sub>CE(sat)</sub>	– – – –	0.004 0.037 0.060 0.072	0.010 0.050 0.090 0.100	V
Base – Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 10 mA)	V <sub>BE(sat)</sub>	–	0.760	0.900	V
Base – Emitter Turn-on Voltage (Note 3) (I <sub>C</sub> = 1.0 A, V <sub>CE</sub> = 2.0 V)	V <sub>BE(on)</sub>	–	0.760	0.900	V
Cutoff Frequency (I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 5.0 V, f = 100 MHz)	f <sub>T</sub>	150	–	–	MHz
Input Capacitance (V <sub>EB</sub> = 0.5 V, f = 1.0 MHz)	C <sub>ibo</sub>	–	–	450	pF
Output Capacitance (V <sub>CB</sub> = 3.0 V, f = 1.0 MHz)	C <sub>obo</sub>	–	–	45	pF

### SWITCHING CHARACTERISTICS

Delay (V <sub>CC</sub> = 15 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA)	t <sub>d</sub>	–	–	100	ns
Rise (V <sub>CC</sub> = 15 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA)	t <sub>r</sub>	–	–	100	ns
Storage (V <sub>CC</sub> = 15 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA)	t <sub>s</sub>	–	–	500	ns
Fall (V <sub>CC</sub> = 15 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA)	t <sub>f</sub>	–	–	110	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

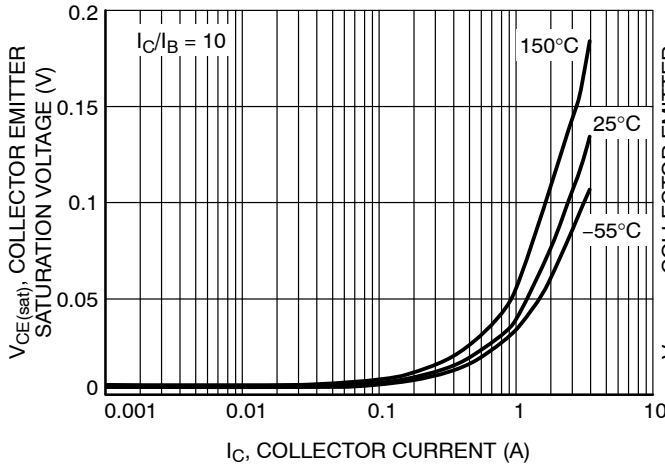


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

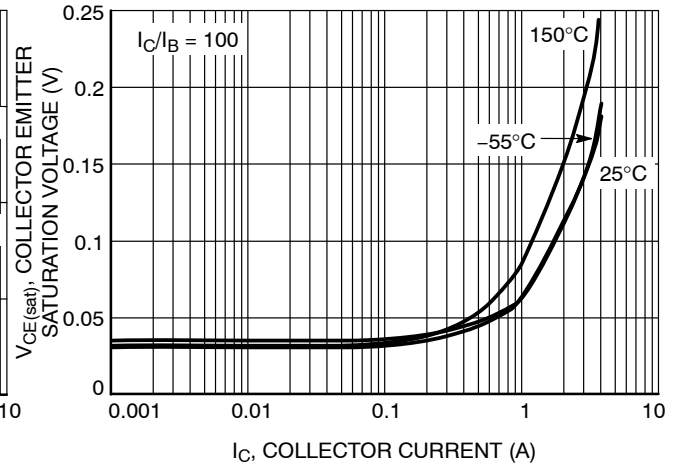


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

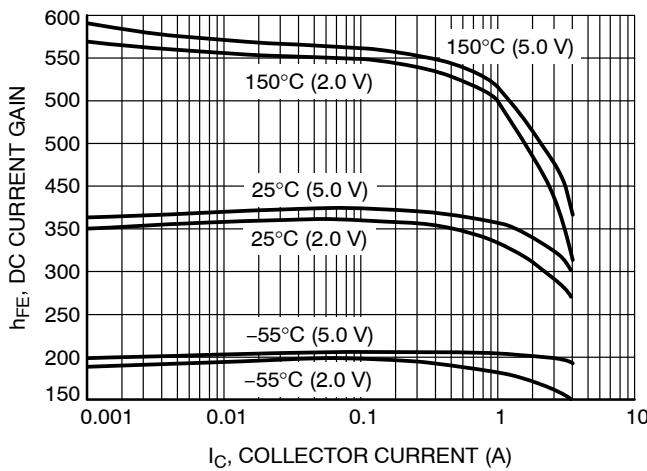


Figure 3. DC Current Gain vs. Collector Current

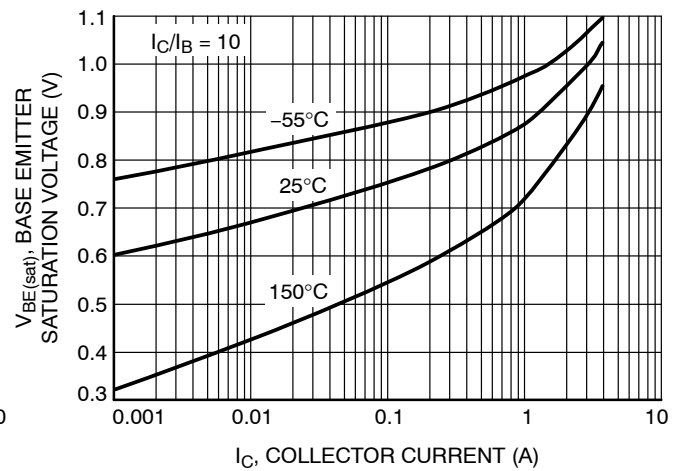


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

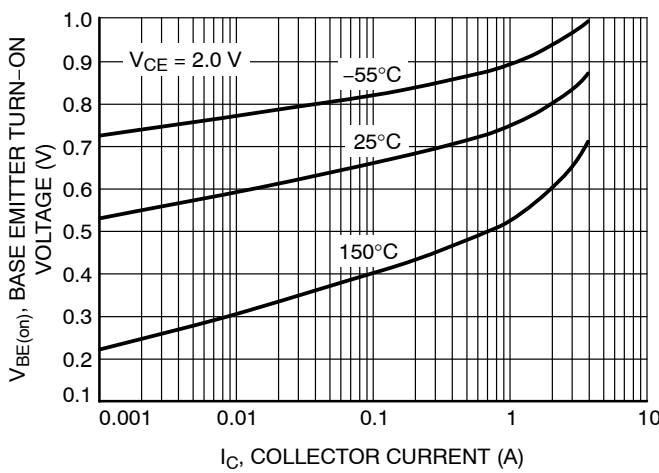


Figure 5. Base Emitter Turn-On Voltage vs. Collector Current

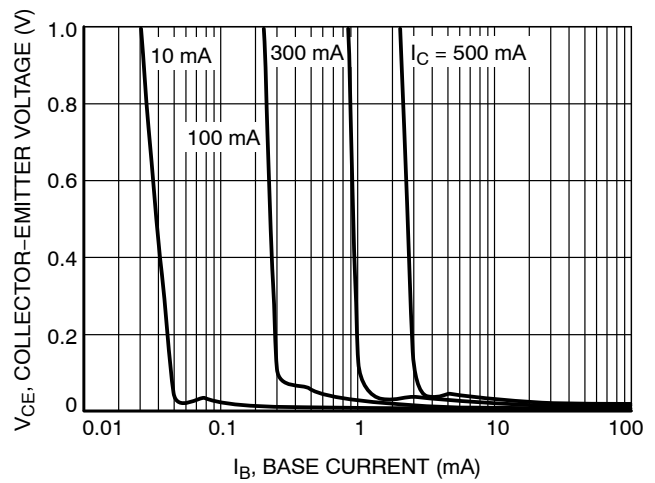


Figure 6. Saturation Region

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## TYPICAL CHARACTERISTICS

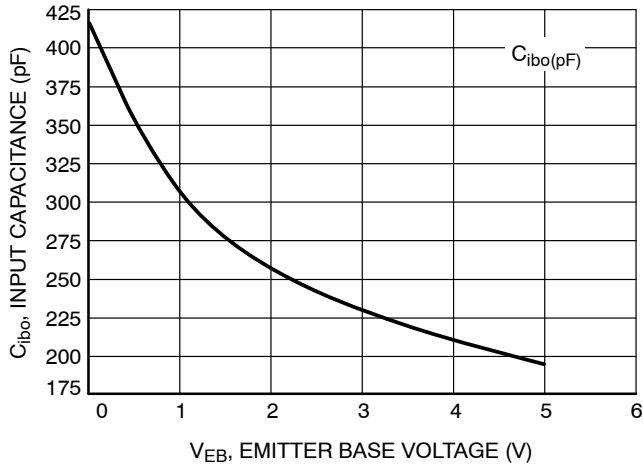


Figure 7. Input Capacitance

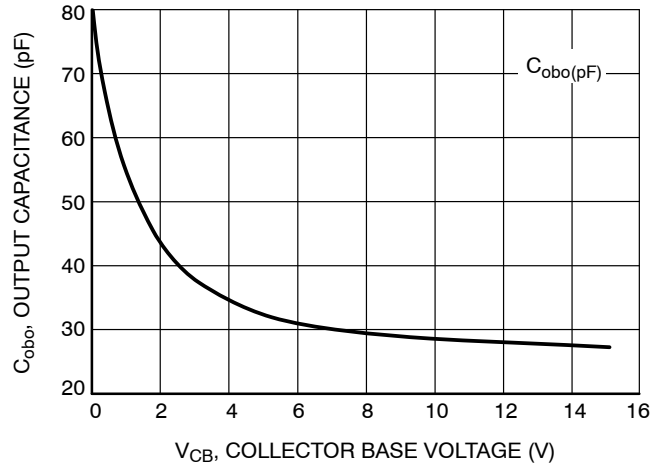


Figure 8. Output Capacitance

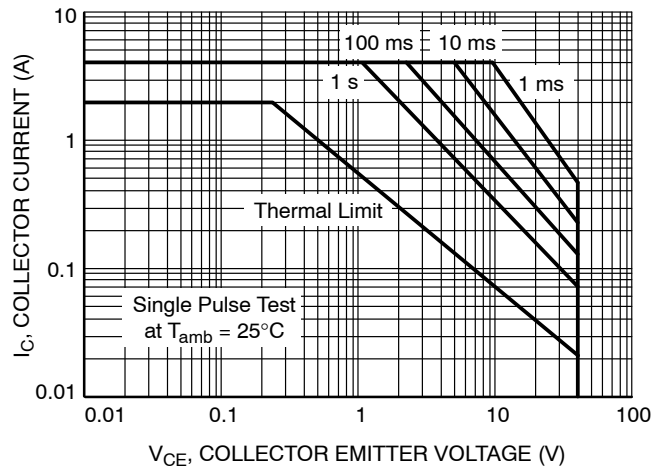
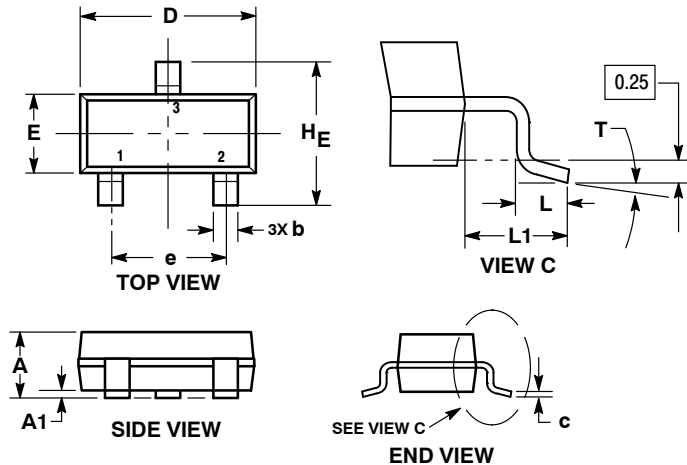


Figure 9. Safe Operating Area

# NSS20201LT1G, NSV20201LT1G

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AR



**NOTES:**

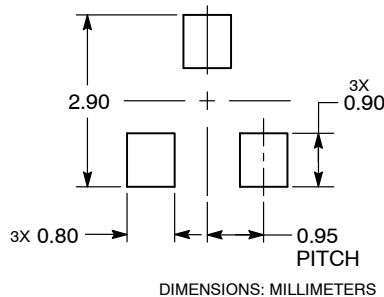
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**STYLE 6:**

1. BASE
2. EMITTER
3. COLLECTOR

### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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